

Silicon Carbide Diode 6 January 2017

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO220F-2L plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quic	k reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{F(AV)}	average forward current	$\begin{array}{l} \delta = 0.5 \hspace{0.2cm} ; \hspace{0.2cm} T_h \leq \hspace{0.2cm} 25 \hspace{0.2cm} ^{\circ} C; \hspace{0.2cm} square-wave \\ \text{pulse;} \hspace{0.2cm} \underset{Fig. \hspace{0.1cm} 1; \hspace{0.1cm} Fig. \hspace{0.1cm} 2; \hspace{0.1cm} Fig. \hspace{0.1cm} 3; \hspace{0.1cm} \underset{Fig. \hspace{0.1cm} 4}{I} \end{array}$	-	-	10	A
Tj	junction temperature		-	-	175	°C
Static chara	cteristics	·				_
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
Dynamic cha	aracteristics	·				

Silicon Carbide Diode

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Qr	recovered charge	$I_{F} = 10 \text{ A; } dI_{F}/dt = 500 \text{ A}/\mu\text{s;}$ $V_{R} = 400 \text{ V; } T_{j} = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	15	-	nC

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	٦	K A
2	А	anode	© O ⊚	001aaa020
mb	n.c.	mounting base; isolated	TO220F-2L	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
NXPSC10650X	-	Plastic single-ended through-hole package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F	TO220F-2L				

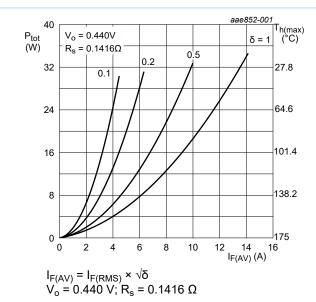
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7. Limiting values

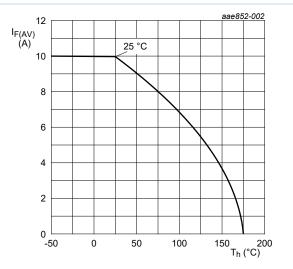
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	650	V
V _{RWM}	crest working reverse voltage		-	650	V
V _R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 25 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	10	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $\ ; t_p$ = 25 µs; $T_h \leq \ 25 \ ^\circ C;$ squarewave pulse	-	20	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	50	А
forwa	forward current	t _p = 10 μs; T _{j(init)} = 25 °C; square-wave pulse	-	450	A
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C





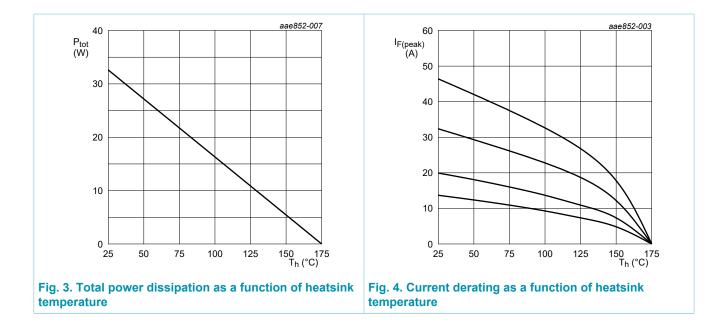




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NXPSC10650X

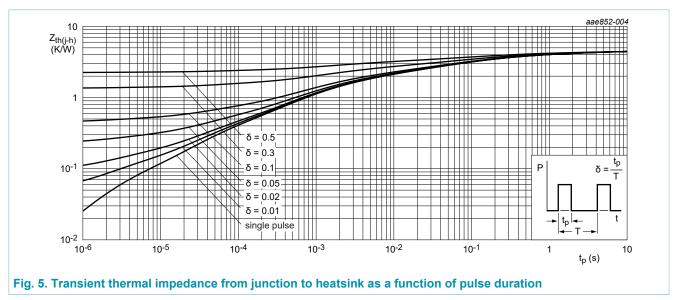
Silicon Carbide Diode



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8. Thermal characteristics

able 5. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5		-	-	4.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air		-	55	-	K/W



9. Isolation characteristics

Table 6. Isolation	on characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; T _h = 25 °C; RH = 65 %	-	-	2500	V

Table 5 Thermal characteristics

Silicon Carbide Diode

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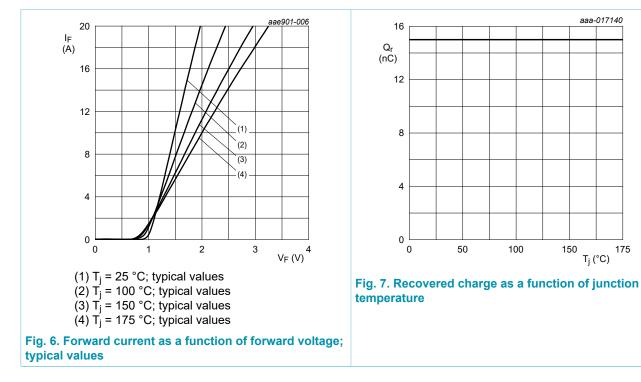
175 T_j (°C)

150

100

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · ·			
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C	-	-	250	μA
		V _R = 650 V; T _j = 150 °C	-	-	800	μA
Dynamic ch	naracteristics	· ·				
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 7</u>	-	15	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	300	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	34	-	pF
		f = 1 MHz; V _R = 600 V; T _i = 25 °C	-	28	-	pF



Silicon Carbide Diode

11. Package outline

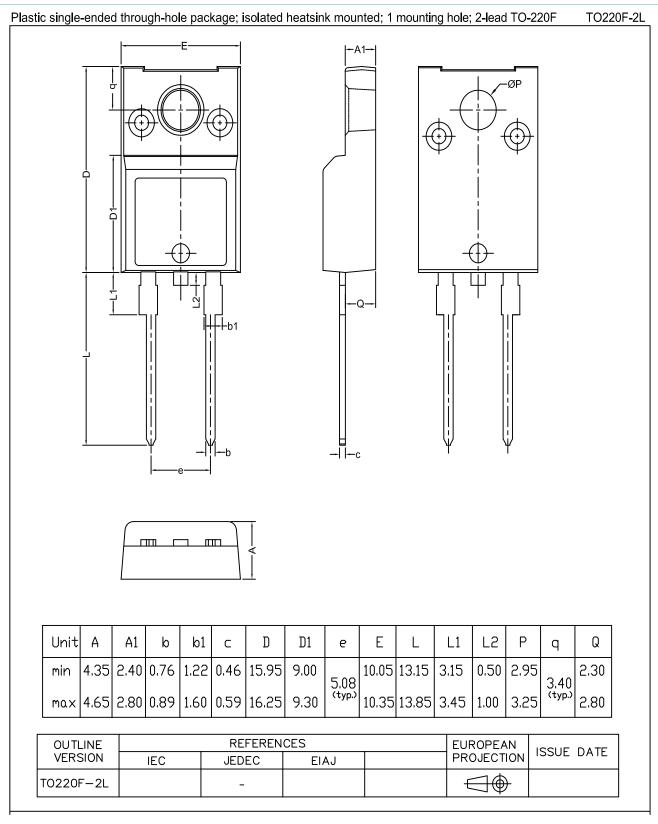


Fig. 8. Package outline TO220F-2L

Silicon Carbide Diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Silicon Carbide Diode

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13. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	3
8.	Thermal characteristics	5
9.	Isolation characteristics	5
10.	Characteristics	6
11.	Package outline	7
12.	Legal information	8

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